

# HL6333MG/34MG

Low Operating Current Visible Laser Diode

ODE-208-033A (Z) Rev.1 Oct. 21, 2005

## Description

The HL6333MG/34MG are 0.63  $\mu$ m band AlGaInP 10mW laser diodes with a multi-quantum well (MQW) structure. They are suitable as light sources for laser levelers, laser scanners and optical equipment for measurement.

#### Features

- Visible light output:  $\lambda p = 635 \text{ nm Typ}$
- Single longitudinal mode
- Optical output power: 10 mW CW
- Low operating current : 55 mA Typ
- Low Operating voltage: 2.4 V Max
- Operating temperature  $:+50^{\circ}C$
- TM mode oscillation

#### **Absolute Maximum Ratings**

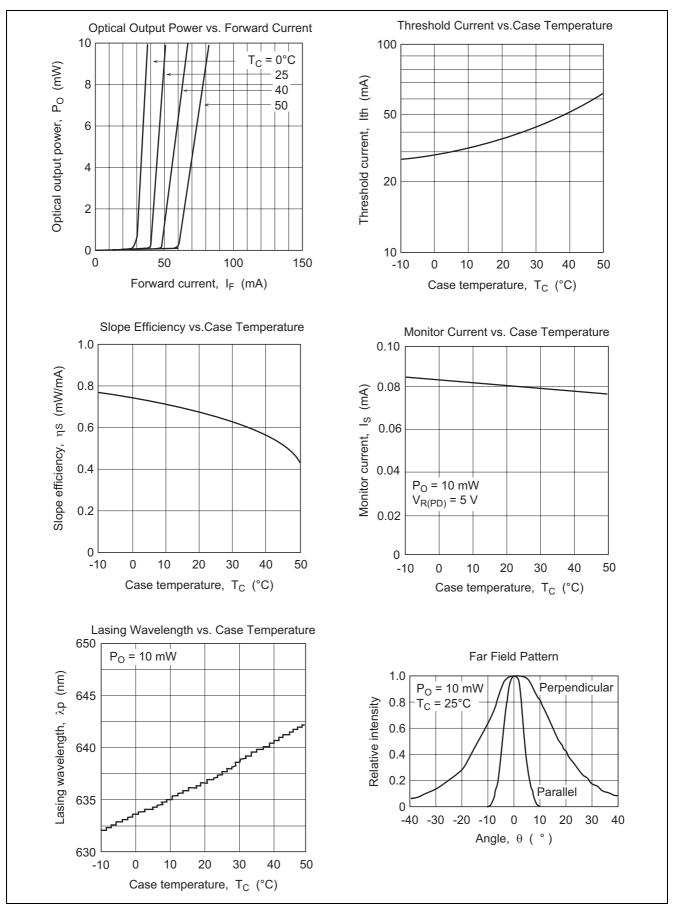
Package Type	Internal Circuit	Internal Circuit	
• HL6333MG/34MG: MG	• HL6333MG	• HL6334MG	
F			

			$(T_{C} = 25^{\circ}C)$
Item	Symbol	Ratings	Unit
Optical output power	Po	10	mW
LD reverse voltage	V <sub>R(LD)</sub>	2	V
PD reverse voltage	V <sub>R(PD)</sub>	30	V
Operating temperature	Topr	-10 to +50	°C
Storage temperature	Tstg	-40 to +85	°C

## **Optical and Electrical Characteristics**

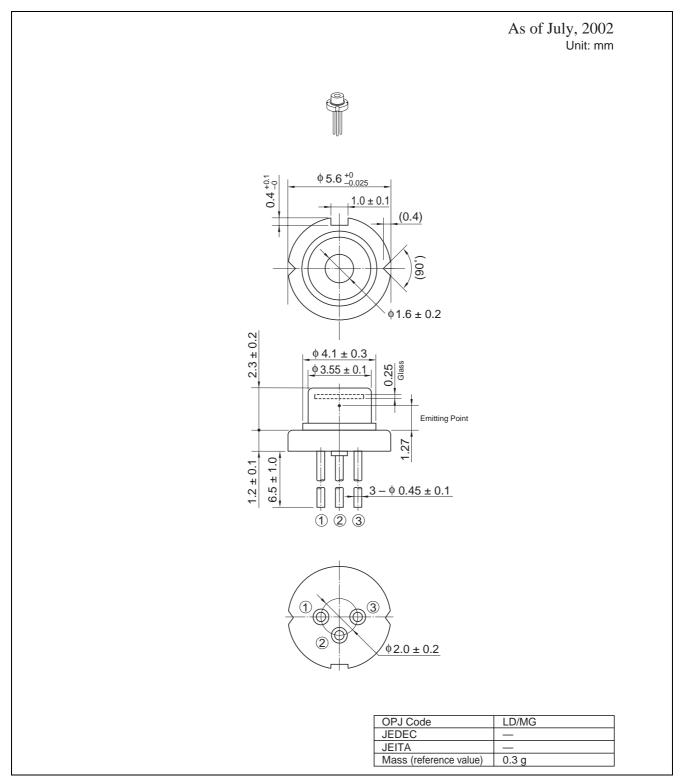
 $(T_C = 25^{\circ}C)$ Symbol **Test Conditions** Item Min Тур Max Unit Threshold current lth 40 60 mΑ \_\_\_\_ 55 75 mΑ  $P_0 = 10 \text{ mW}$ Operating current lop Operating voltage 2.2 2.4 V  $P_0 = 10 \text{ mW}$ VOP Slope efficiency 0.90 6 (mW) / (I<sub>(8mW)</sub> - I<sub>(2mW)</sub>) 0.40 0.65 mW/mA ηs Beam divergence θ// 6 8 11  $P_0 = 10 \text{ mW}$ parallel to the junction Beam divergence θ⊥ 25 31 36 o  $P_0 = 10 \text{ mW}$ perpendicular to the junction 630 635 640  $P_0 = 10 \text{ mW}$ Lasing wavelength λp nm Monitor current  $I_S$ 0.04 0.08 0.16 mΑ  $P_{O} = 10 \text{ mW}, V_{R(PD)} = 5 \text{ V}$ 

# **Typical Characteristic Curves**





# **Package Dimensions**





#### Cautions

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- 1. The laser light is harmful to human body especially to eye no matter what directly or indirectly. The laser beam shall be observed or adjusted through infrared camera or equivalent.
- 2. This product contains gallium arsenide (GaAs), which may seriously endanger your health even at very low doses. Please avoid treatment which may create GaAs powder or gas, such as disassembly or performing chemical experiments, when you handle the product.

When disposing of the product, please follow the laws of your country and separate it from other waste such as industrial waste and household garbage.

3. Definition of items shown in this CAS is in accordance with that shown in Opto Device Databook issued by OPJ unless otherwise specified.

# **Sales Offices**



#### Device Business Unit Opnext Japan, Inc.

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